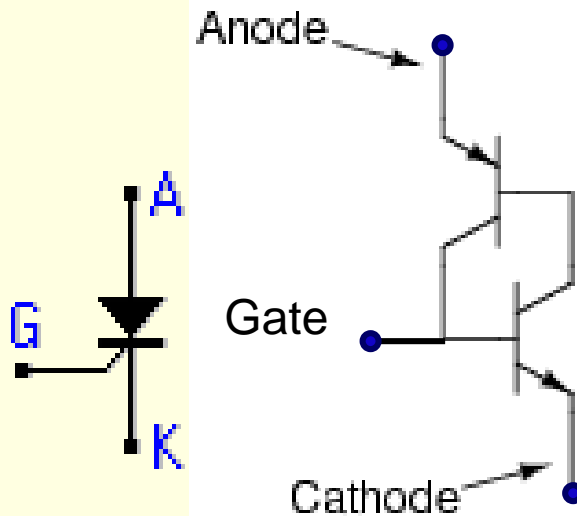
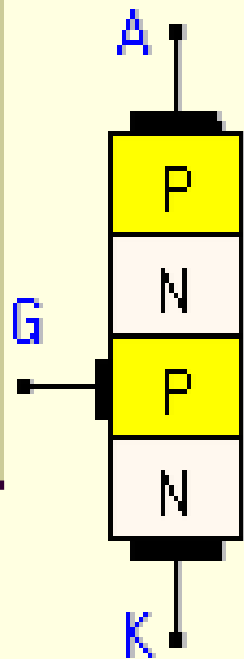




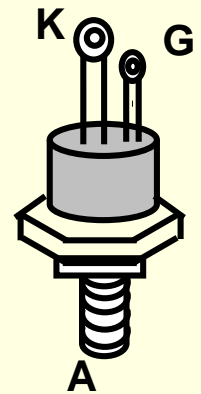
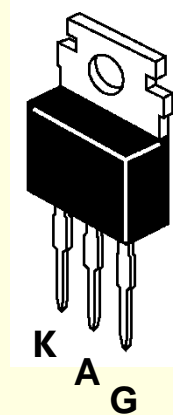
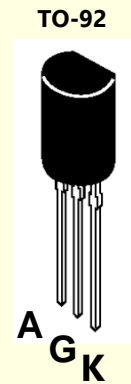
# CHƯƠNG 3

## HỢI LINH KIẾN 4 LỚP

# SCR (SILICON CONTROLLED RECTIFIER)

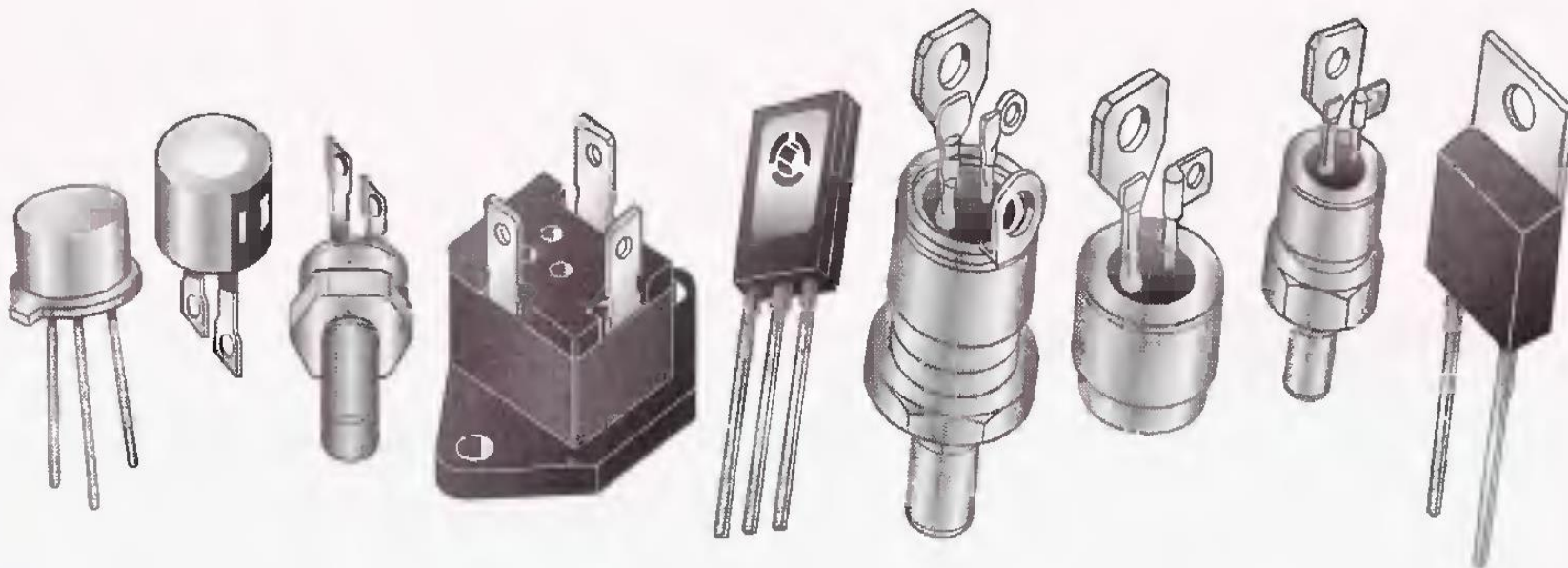


*Equivalent schematic*



# SCR (SILICON CONTROLLED RECTIFIER)

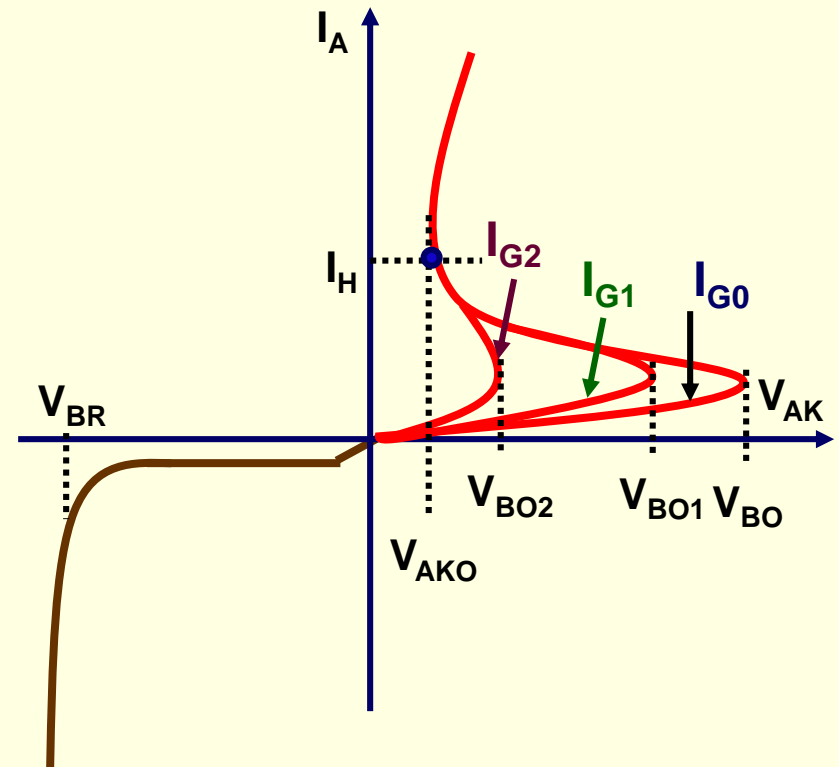
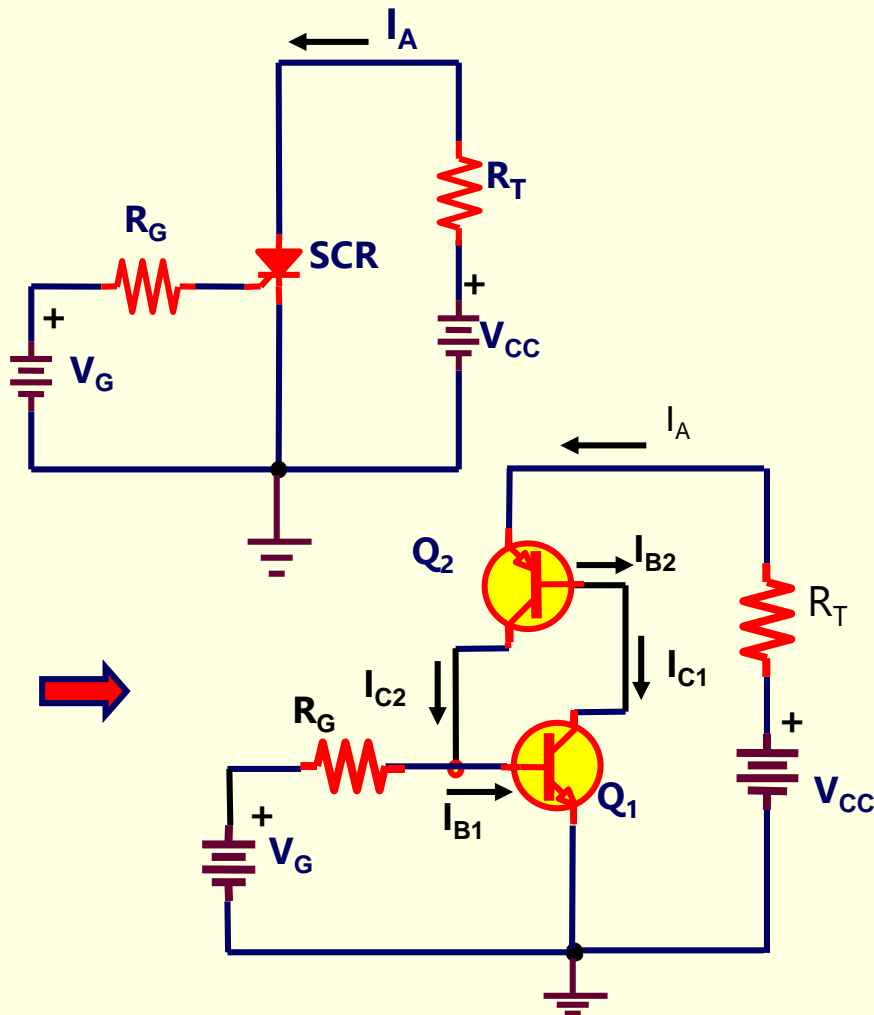
## HÌNH DẠNG THỰC TẾ :



(c) Typical packages

# SCR (SILICON CONTROLLED RECTIFIER)

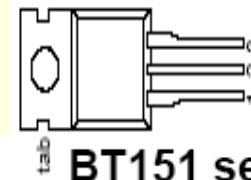
## NGUYÊN LÝ VÀ ĐẶC TÍNH :



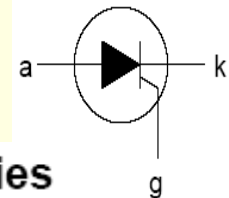
# SCR (SILICON CONTROLLED RECTIFIER)

## DATASHEET:

1 cathode  
2 anode  
3 gate  
tab anode



**BT151 series**



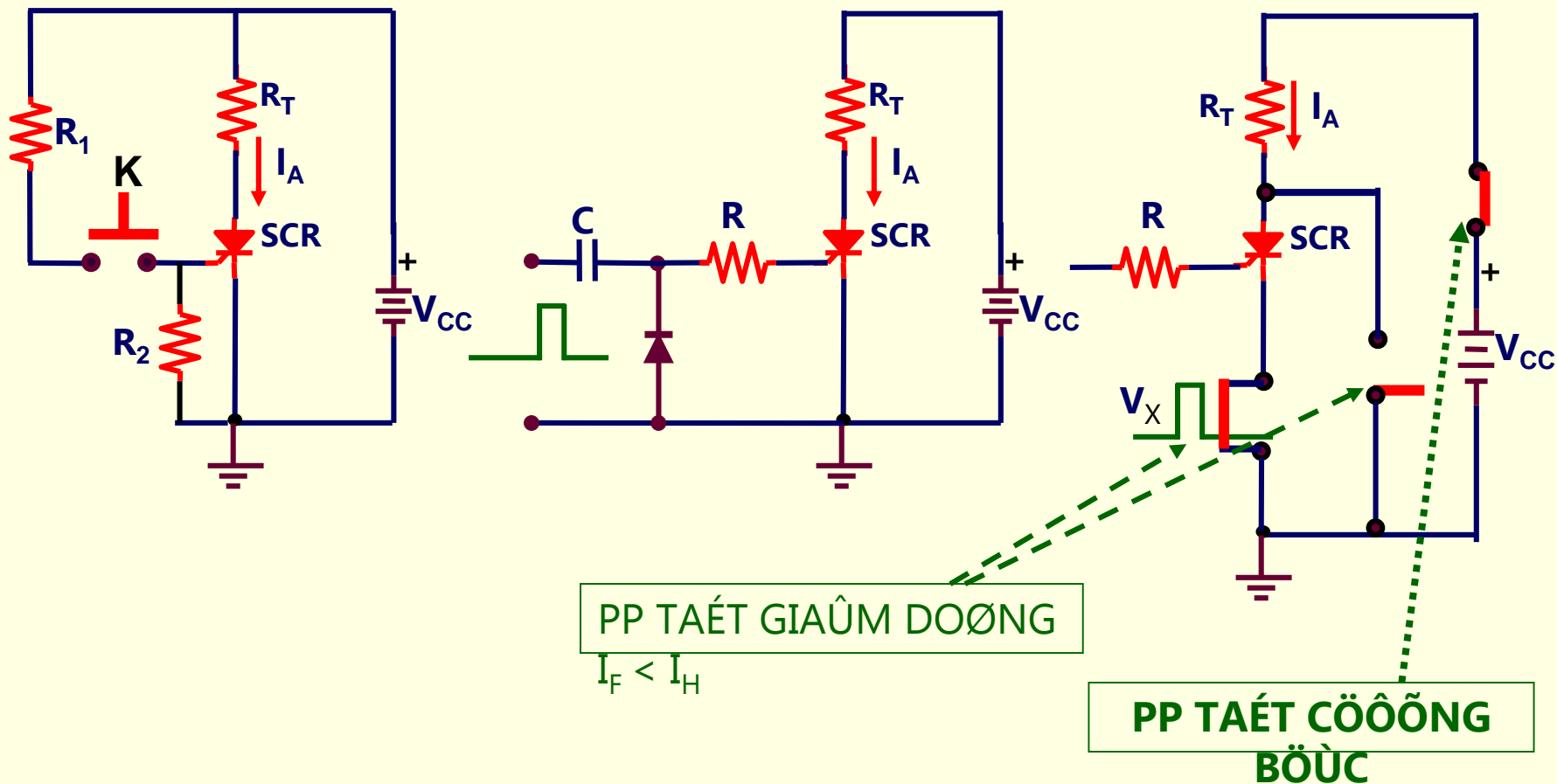
## LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
$V_{DRM}, V_{RRM}$	Repetitive peak off-state voltages		-	-500R 500 <sup>1</sup>	-650R 650 <sup>1</sup>	-800R 800	V
$I_{T(AV)}$	Average on-state current	half sine wave; $T_{mb} \leq 109\text{ }^{\circ}\text{C}$	-	7.5			A
$I_{T(RMS)}$	RMS on-state current	all conduction angles	-	12			A
$I_{TSM}$	Non-repetitive peak on-state current	half sine wave; $T_j = 25\text{ }^{\circ}\text{C}$ prior to surge	-	100			A
		$t = 10\text{ ms}$	-	110			A
$I^2t$	$I^2t$ for fusing	$t = 8.3\text{ ms}$	-	50			A <sup>2</sup> s
$dI_T/dt$	Repetitive rate of rise of on-state current after triggering	$t = 10\text{ ms}$ $I_{TM} = 20\text{ A}; I_G = 50\text{ mA};$ $dI_G/dt = 50\text{ mA}/\mu\text{s}$	-	50			A/ $\mu\text{s}$
$I_{GM}$	Peak gate current		-	2			A
$V_{GM}$	Peak gate voltage		-	5			V
$V_{RGM}$	Peak reverse gate voltage		-	5			V
$P_{GM}$	Peak gate power		-	5			W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	0.5			W
$T_{stg}$	Storage temperature		-40	150			$^{\circ}\text{C}$
$T_j$	Operating junction temperature		-	125			$^{\circ}\text{C}$

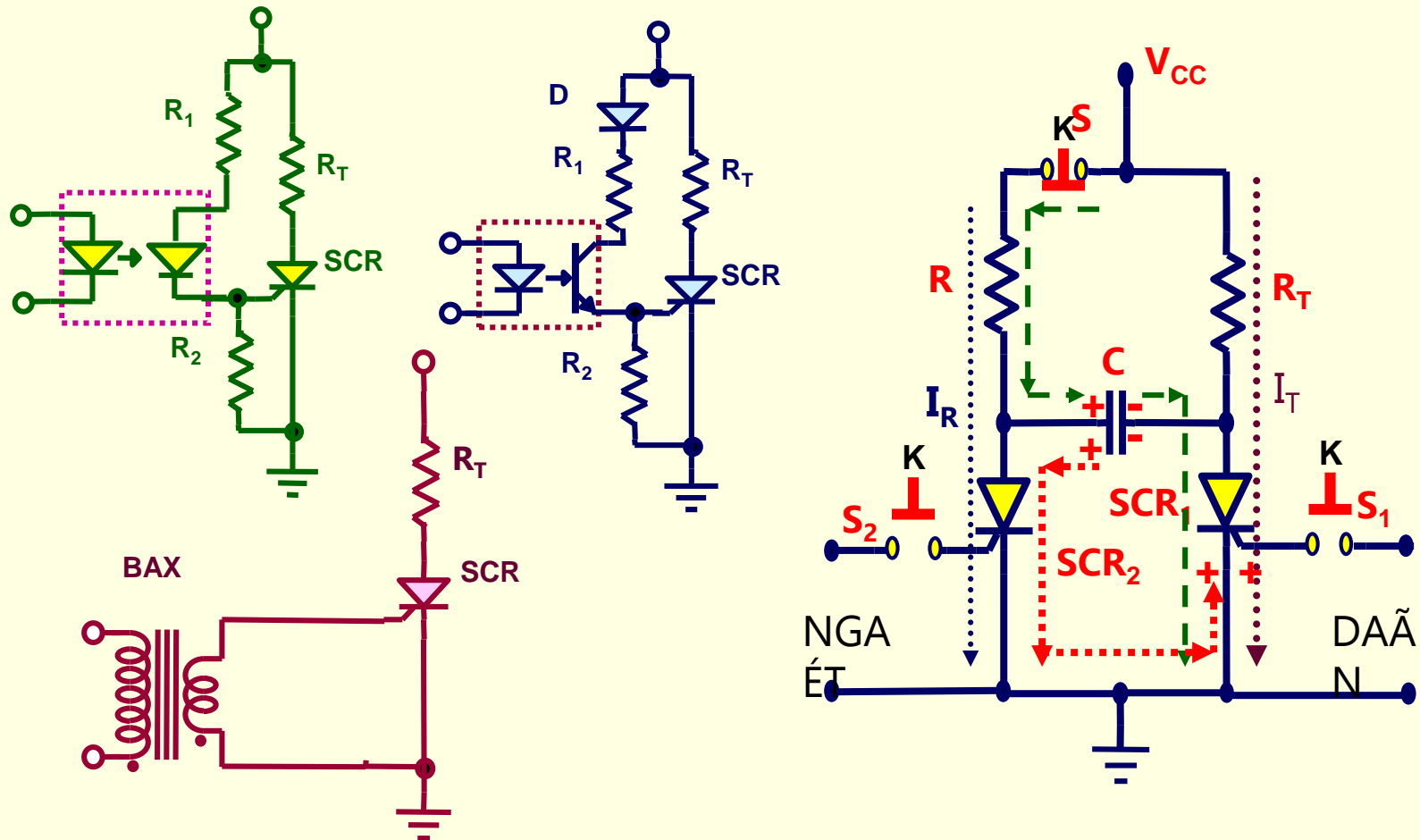
# SCR (SILICON CONTROLLED RECTIFIER)

## CÁC PHƯƠNG PHÁP KÍCH DẪN VÀ NGẮT SCR VỚI NGUỒN DC:



# SCR (SILICON CONTROLLED RECTIFIER)

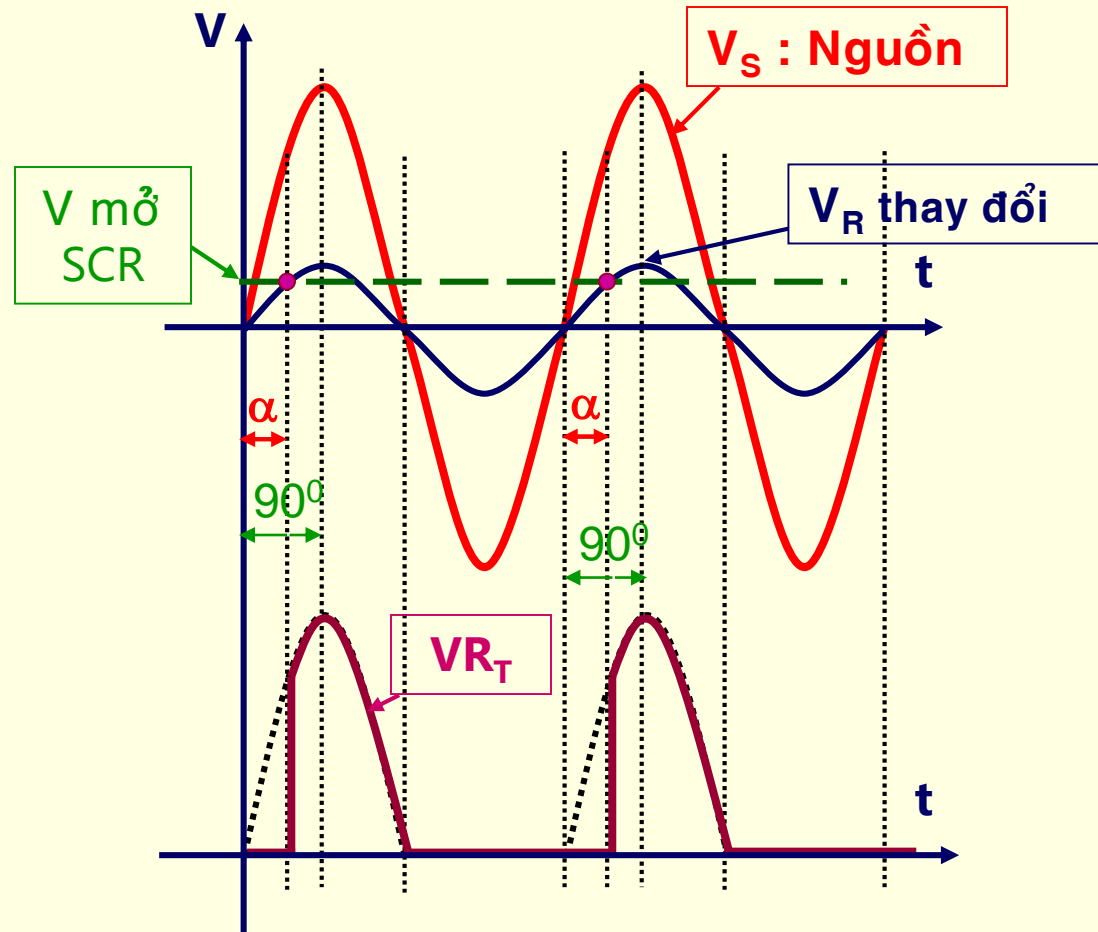
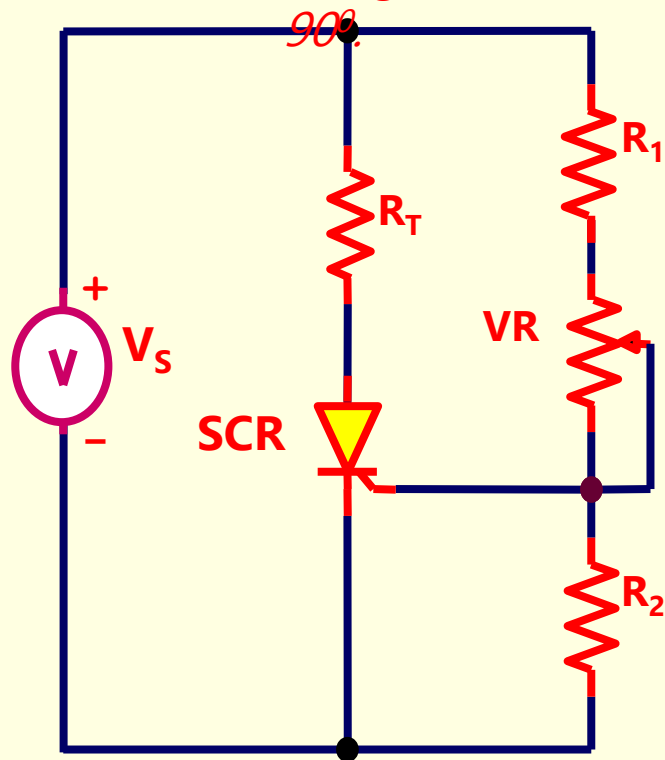
CAÙC PHÖÔNG PHÁP KÍCH DẪN VÀO NGẮT SCR VỚI NGUỒN DC:



# SCR (SILICON CONTROLLED RECTIFIER)

## CÁC PHƯƠNG PHÁP ĐIỀU KHIỂN SCR CƠ BẢN VỚI NGUỒN AC:

*Kích SCR vào với góc  $\alpha < 90^\circ$*

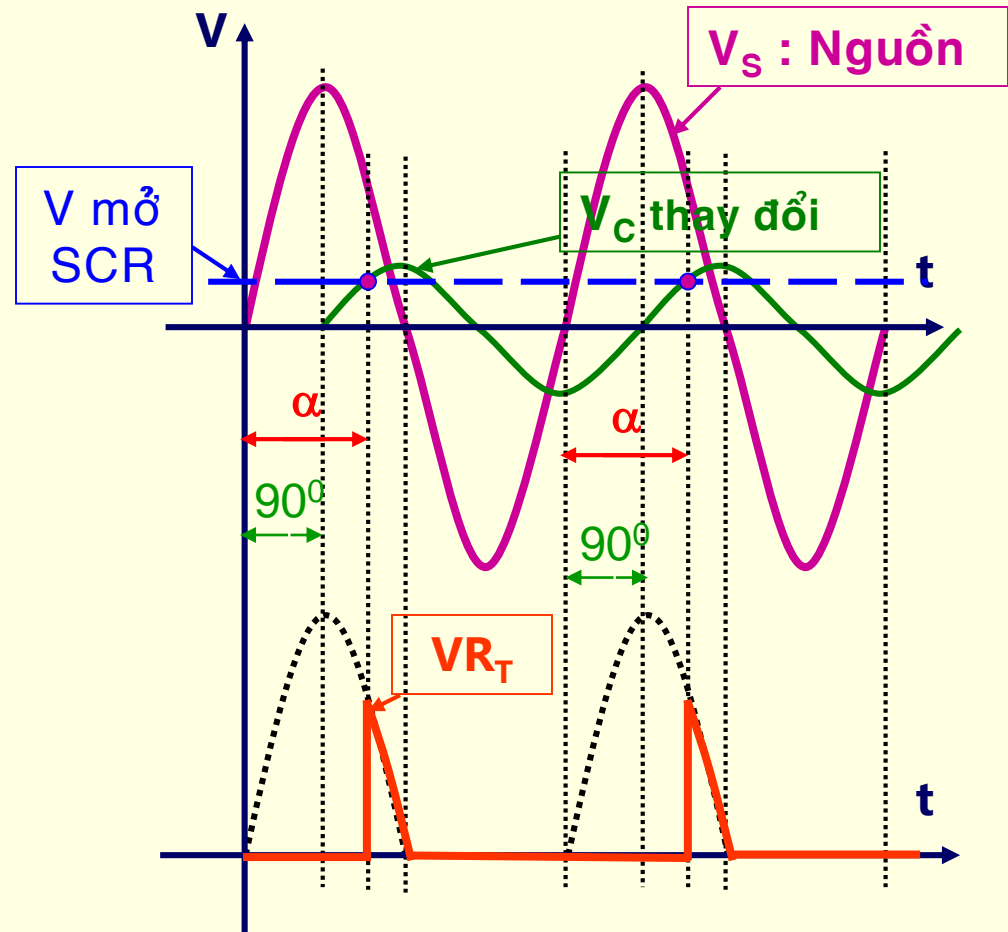
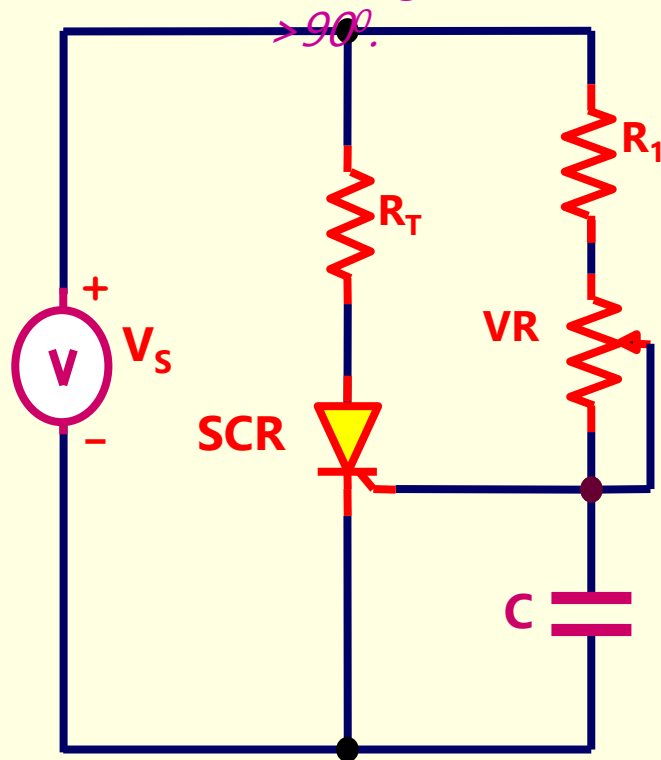




# SCR (SILICON CONTROLLED RECTIFIER)

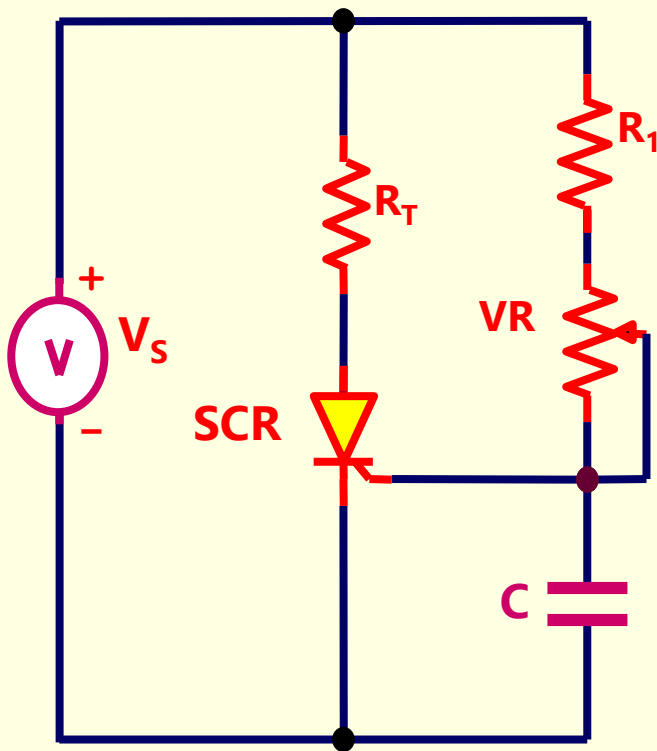
## CAÙC PHÖÔNG PHÁP ÑIEÀU KHIỂN SCR CÔ BAÙN VÖÙI NGUỒN AC:

*Kích SCR vöùt goùc  $\alpha$*



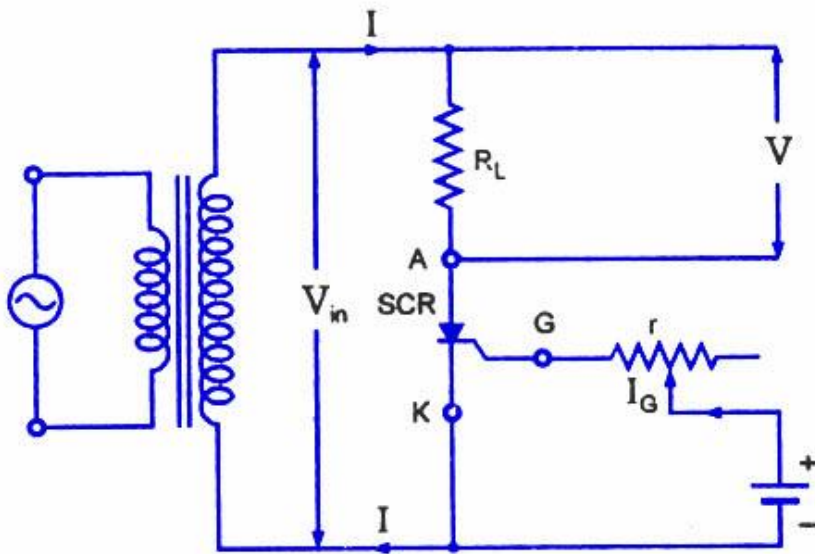
# SCR (SILICON CONTROLLED RECTIFIER)

**Vd: Vẽ dạng sóng điện áp trên tải khi  $\alpha = 120^\circ$ . Tính điện áp trung bình trên tải.  
Biết  $V_s = 50\sin 100\pi t$  (V)**

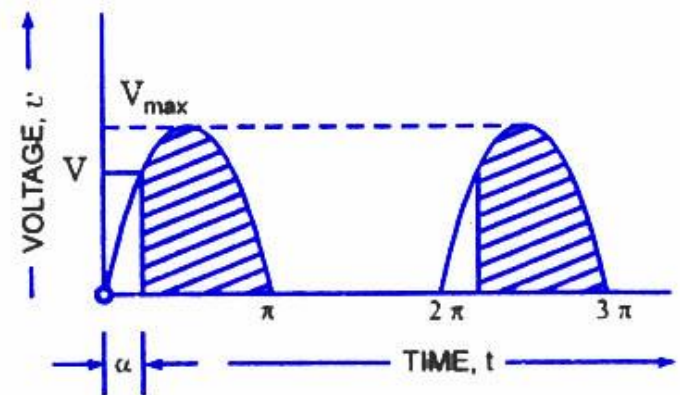


# SCR (SILICON CONTROLLED RECTIFIER)

## ỨNG DỤNG



*Circuit Diagram*

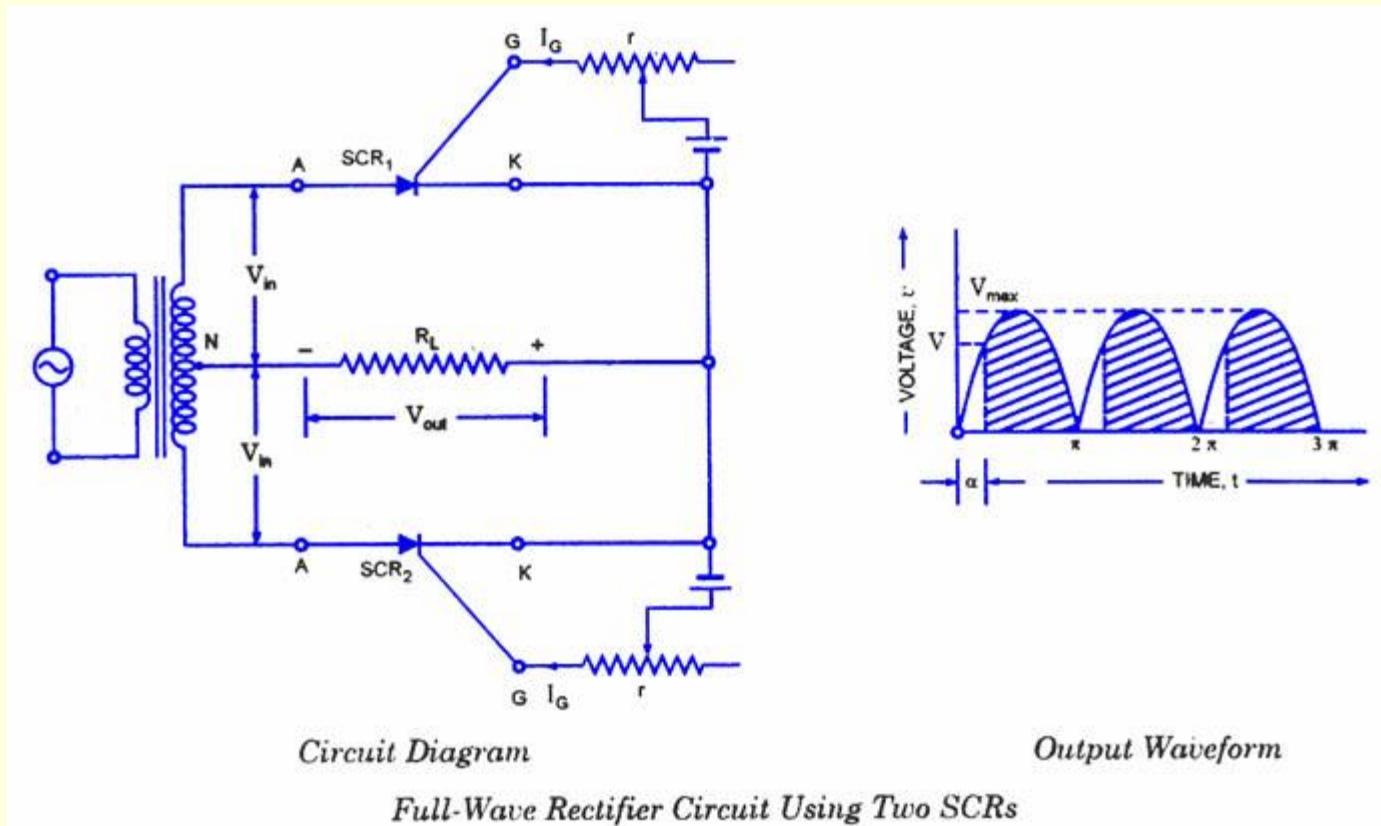


*Output Waveform*

*SCR As Half-Wave Rectifier*

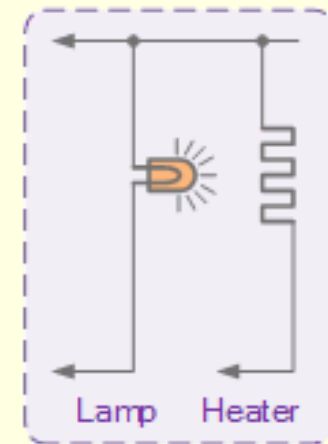
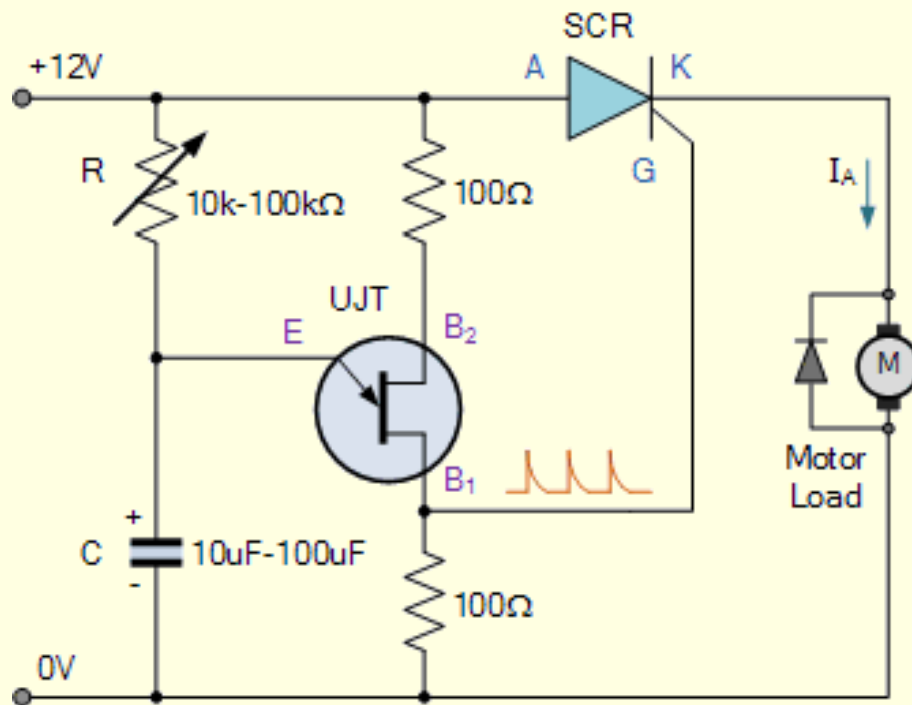
# SCR (SILICON CONTROLLED RECTIFIER)

## ỨNG DỤNG



# SCR (SILICON CONTROLLED RECTIFIER)

## ỨNG DỤNG



Different AC Loads